NOVEMBER 1986 - REVISED SEPTEMBER 1997

#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Non-repetitive peak on-state pulse current (see Notes 1, 2 and 3)			
8/20 μs (ANSI C62.41, open-circuit voltage wave shape 1.2/50 μs)	I <sub>TSP</sub>	150	
10/160 μs (FCC Part 68, open-circuit voltage wave shape 10/160 μs)		60	
5/200 μs (VDE 0433, open-circuit voltage wave shape 2 kV, 10/700 μs)		50	
0.2/310 μs (RLM 88, open-circuit voltage wave shape 1.5 kV, 0.5/700 μs)	I <sub>TSP</sub>	38	А
5/310 μs (CCITT IX K17/K20, open-circuit voltage wave shape 2 kV, 10/700 μs)	_	50	
5/310 μs (FTZ R12, open-circuit voltage wave shape 2 kV, 10/700 μs)		50	
10/560 μs (FCC Part 68, open-circuit voltage wave shape 10/560 μs)		45	
10/1000 μs (REA PE-60, open-circuit voltage wave shape 10/1000 μs)		50	
Non-repetitive peak on-state current, 50 Hz, 2.5 s (see Notes 1 and 2)	I <sub>TSM</sub>	10	A rms
Initial rate of rise of on-state current, Linear current ramp, Maximum ramp value < 38 A	di <sub>T</sub> /dt	250	A/µs
Junction temperature	TJ	150	°C
Operating free - air temperature range		0 to 70	°C
Storage temperature range	T <sub>stg</sub>	-40 to +150	°C
Lead temperature 1.5 mm from case for 10 s	T <sub>lead</sub>	260	°C

NOTES: 1. Above 70°C, derate linearly to zero at 150°C case temperature

2. This value applies when the initial case temperature is at (or below) 70°C. The surge may be repeated after the device has returned to thermal equilibrium.

3. Most PTT's quote an unloaded voltage waveform. In operation the TISP essentially shorts the generator output. The resulting loaded current waveform is specified.

#### electrical characteristics for the A and B terminals, $T_J = 25^{\circ}C$

	PARAMETER		TEST CONDIT	IONS	MIN	TYP	MAX	UNIT
V <sub>7</sub>	Reference zener	$I_{z} = \pm 1 mA$			± 145			V
٧Z	voltage	$I_Z = \perp IIII_A$			145			v
Ι <sub>D</sub>	Off-state leakage	V <sub>D</sub> = ± 50 V					± 10	μA
	current	vD = 7 20 v					± 10	μΑ
C <sub>off</sub>	Off-state capacitance	$V_D = 0$	f = 1 kHz	(see Note 4)		40	100	pF

NOTE 4: These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The third terminal is connected to the guard terminal of the bridge.

#### electrical characteristics for the A and C or the B and C terminals, $T_J = 25^{\circ}C$

	PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
Vz	Reference zener voltage	$I_Z = \pm 1 \text{mA}$			± 145			V
∝Vz	Temperature coefficient of reference voltage					0.1		%/ºC
V <sub>(BO)</sub>	Breakover voltage	(see Notes 5 and 6)					± 180	V
I <sub>(BO)</sub>	Breakover current	(see Note 5)			± 0.15		± 0.6	А
V <sub>TM</sub>	Peak on-state voltage	$I_T = \pm 5 A$	(see Notes 5 and 6)			± 2.2	± 3	V
Ι <sub>Η</sub>	Holding current	(see Note 5)			± 150			mA
dv/dt	Critical rate of rise of off-state voltage	(see Note 7)					± 5	kV/μs
۱ <sub>D</sub>	Off-state leakage current	$V_D = \pm 50 V$					± 10	μΑ
C <sub>off</sub>	Off-state capacitance	$V_D = 0$	f = 1 kHz	(see Note 4)		110	200	pF

NOTES: 5. These parameters must be measured using pulse techniques,  $t_w = 100 \ \mu$ s, duty cycle  $\leq 2\%$ .

6. These parameters are measured with voltage sensing contacts separate from the current carrying contacts located within 3.2 mm (0.125 inch) from the device body.

7. Linear rate of rise, maximum voltage limited to 80 % V<sub>Z</sub> (minimum)..

Quadrant I TSF Switching Characteristic TSP L Vz l<sub>z</sub> ۷ Ŀ ۰Ī V<sub>D</sub> V<sub>zv</sub> I<sub>H</sub> (BO) V (BO) . TSM Quadrant III Switching Characteristic TS \_ PMXXAB

#### PARAMETER MEASUREMENT INFORMATION

#### Figure 1. VOLTAGE-CURRENT CHARACTERISTIC FOR ANY PAIR OF TERMINALS

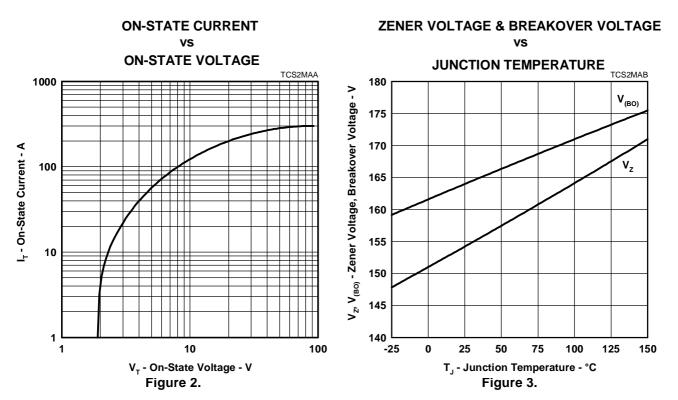
The high level characteristics for terminals A and B are not guaranteed.

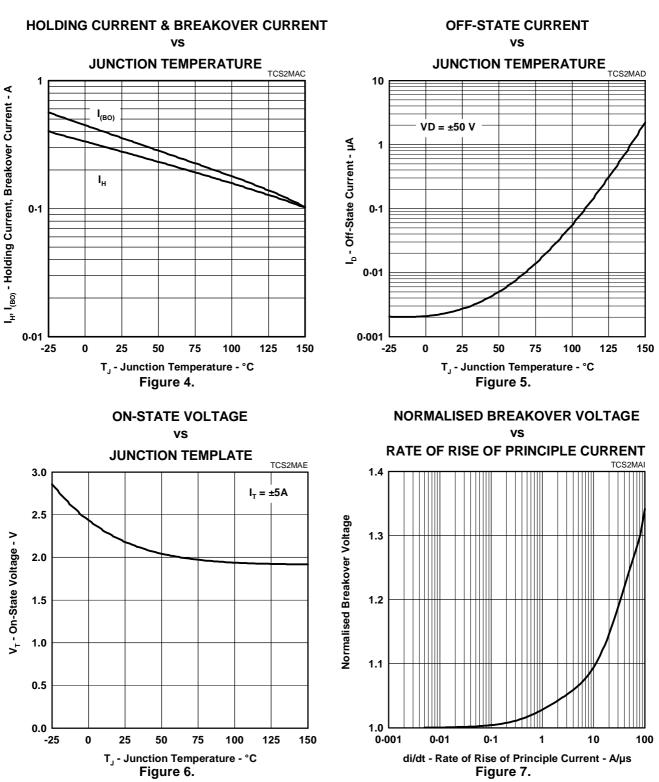
#### thermal characteristics

PARAMETER		TYP	MAX	UNIT
R <sub>0JA</sub> Junction to free air thermal resistance			62.5	°C/W





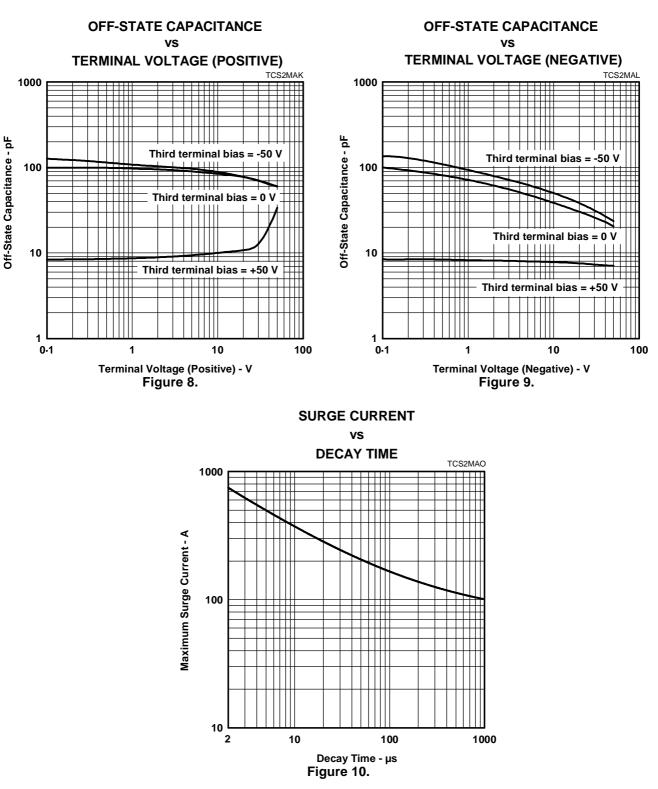




#### TYPICAL CHARACTERISTICS A and C, or B and C terminals

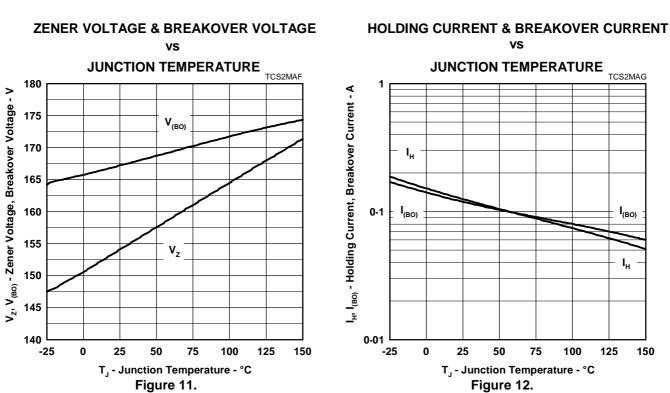


#### TISP2180 DUAL SYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS NOVEMBER 1986 - REVISED SEPTEMBER 1997



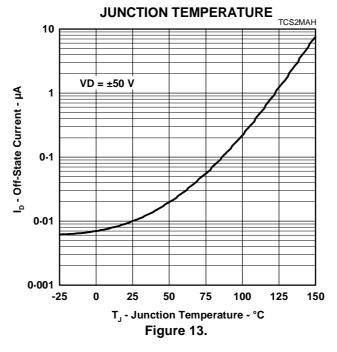
#### TYPICAL CHARACTERISTICS A and C, or B and C terminals

#### TISP2180 DUAL SYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS NOVEMBER 1986 - REVISED SEPTEMBER 1997



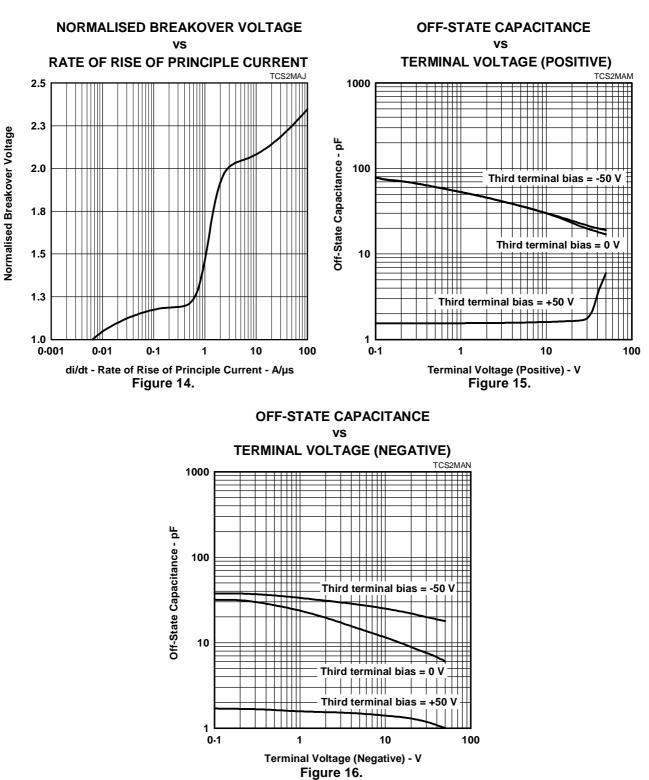
TYPICAL CHARACTERISTICS A and B terminals

> OFF-STATE CURRENT vs



Power D

#### TISP2180 DUAL SYMMETRICAL TRANSIENT VOLTAGE SUPPRESSORS NOVEMBER 1986 - REVISED SEPTEMBER 1997

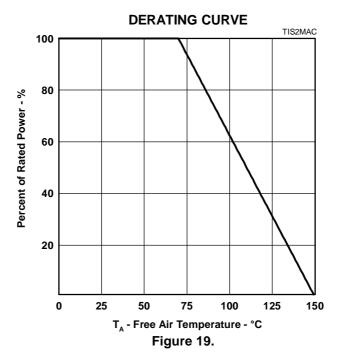


#### TYPICAL CHARACTERISTICS A and B terminals

#### MAXIMUM NON-RECURRENT 50Hz CURRENT vs **CURRENT DURATION** THERMAL RESPONSE TIS2MAB TIS2MAA 10 100 I<sub>RMS</sub> - Maximum Non-Recurrent 50Hz Current - A $Z_{\theta,A}$ - Transient Thermal Impedance - °C/W 1 10 0.1 V<sub>GEN</sub> = 250 V<sub>RMS</sub> R<sub>GEN</sub> = 20 TO 1000 ohms T<sub>AMB</sub> = 70°C 0.01 0.1 0.0001 0.001 0.01 0.1 10 100 1000 0.01 0.1 1 10 100 1 t - Power Pulse Duration - s t - Current Duration - s Figure 17. Figure 18.

#### **THERMAL INFORMATION**

**FREE AIR TEMPERATURE** 



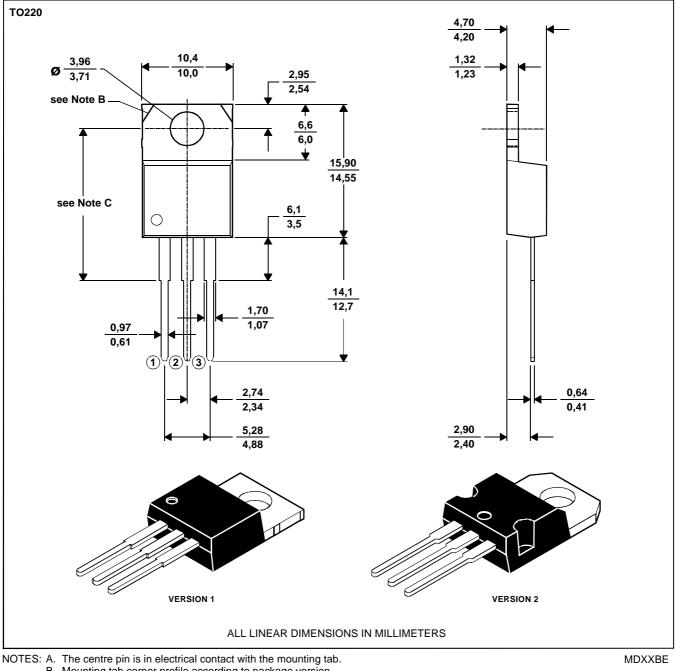


#### **MECHANICAL DATA**

#### **TO-220**

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



B. Mounting tab corner profile according to package version.

C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

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